NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AJT030** is Designed for 960 – 1215 MHz, JTIDS Applications.

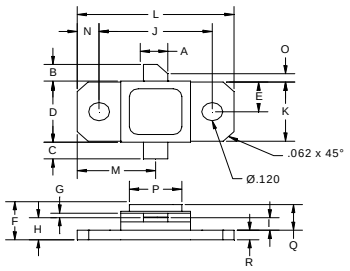
FEATURES:

- Internal Input/Output Matching Network
- $\mathbf{P_G}$ = 7.8 dB at 30 W/ 1215 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

$\mathbf{I_C}$	3.5 A
$\mathbf{V_{CC}}$	40 V
$\mathbf{P_{DISS}}$	75 W @ $T_C \leq 85$ °C
$\mathbf{T_J}$	-65 °C to +250 °C
$\mathbf{T_{STG}}$	-65 °C to +200 °C
$\mathbf{\theta_{JC}}$	2.2 °C/W

PACKAGE STYLE .400 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.140 / 3.56	
B	.110 / 2.80	
C	.110 / 2.80	
D	.395 / 10.03	.407 / 10.34
E	.193 / 4.90	
F		.230 / 5.84
G	.003 / 0.08	.006 / 0.15
H	.118 / 3.00	.131 / 3.33
I	.063 / 1.60	
J	.650 / 16.51	
K	.386 / 9.80	
L	.900 / 22.86	
M	.450 / 11.43	
N	.125 / 3.18	
O	.050 / 1.27	
P	.405 / 10.29	
Q	.170 / 4.32	
R	.062 / 1.58	

ORDER CODE: ASI10546

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$\mathbf{BV_{CBO}}$	I_C = 10 mA	55			**V**
$\mathbf{BV_{CER}}$	I_C = 20 mA R_{BE} = 10 Ω	55			**V**
$\mathbf{BV_{EBO}}$	I_E = 1.0 mA	3.5			**V**
$\mathbf{I_{CES}}$	V_{CE} = 35 V			5.0	**mA**
$\mathbf{h_{FE}}$	V_{CE} = 5.0 V I_C = 1.0 A	15		150	**---**
$\mathbf{P_G}$ $\mathbf{\eta_C}$	V_{CC} = 50 V P_{OUT} = 30 W f = 960 - 1215 MHz	7.8 40			**dB** **%**